

# SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

# **ECH8411**— General-Purpose Switching Device Applications

#### **Features**

- · Ultrahigh-speed switching.
- 1.8V drive.

## **Specifications**

### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		9	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	36	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm²X0.8mm)	1.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.5		1.3	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =4A	7	12		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=4A, VGS=4V		12	16	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =2A, V <sub>GS</sub> =2.5V		16	23	mΩ
	RDS(on)3	ID=2A, VGS=1.8V		25	36	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		1740		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		310		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		290		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		30		ns
Rise Time	tr	See specified Test Circuit.		170		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		240		ns
Fall Time	tf	See specified Test Circuit.		210		ns

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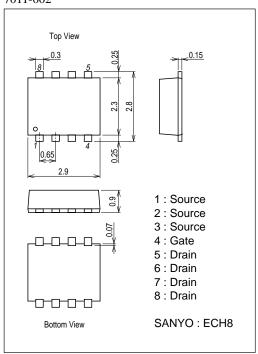
# **ECH8411**

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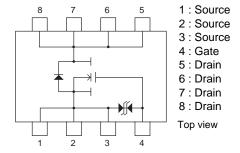
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =9A		21		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =9A		3.5		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =9A		6.2		nC
Diode Forward Voltage	VSD	IS=9A, VGS=0V		0.84	1.2	V

# **Package Dimensions**

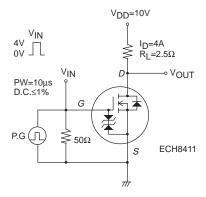
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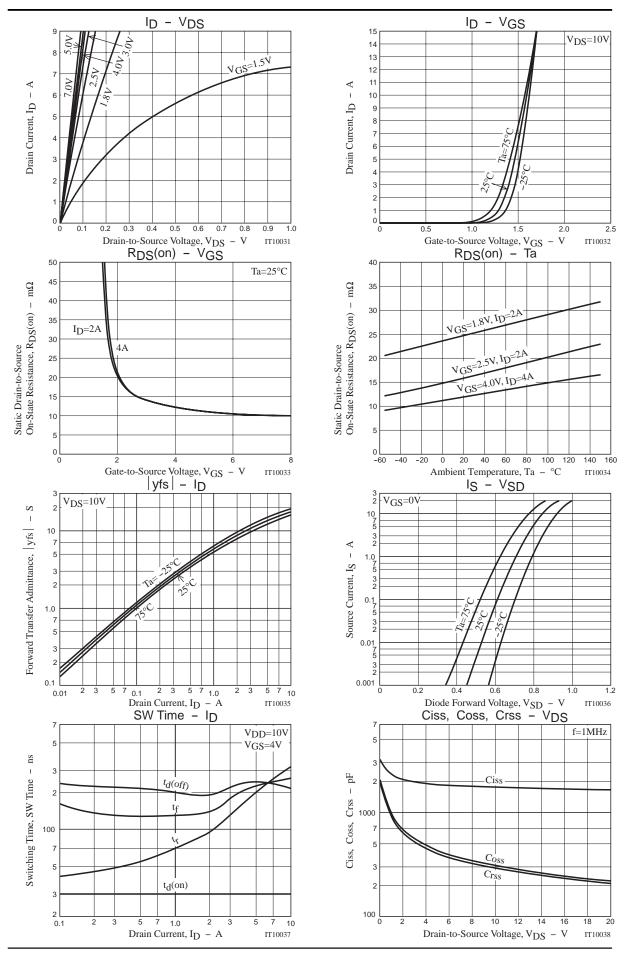


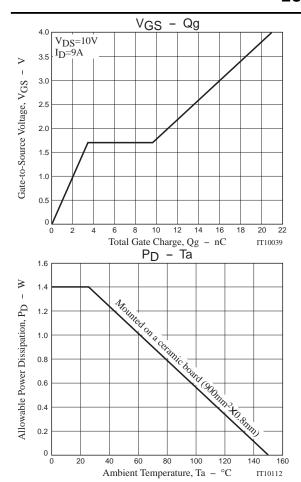
# **Electrical Connection**

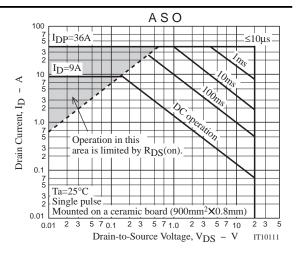


# **Switching Time Test Circuit**









Note on usage: Since the ECH8411 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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